1. Scope

The present specifications shall apply to Sanken silicon diode, EP01C.

2. Outline

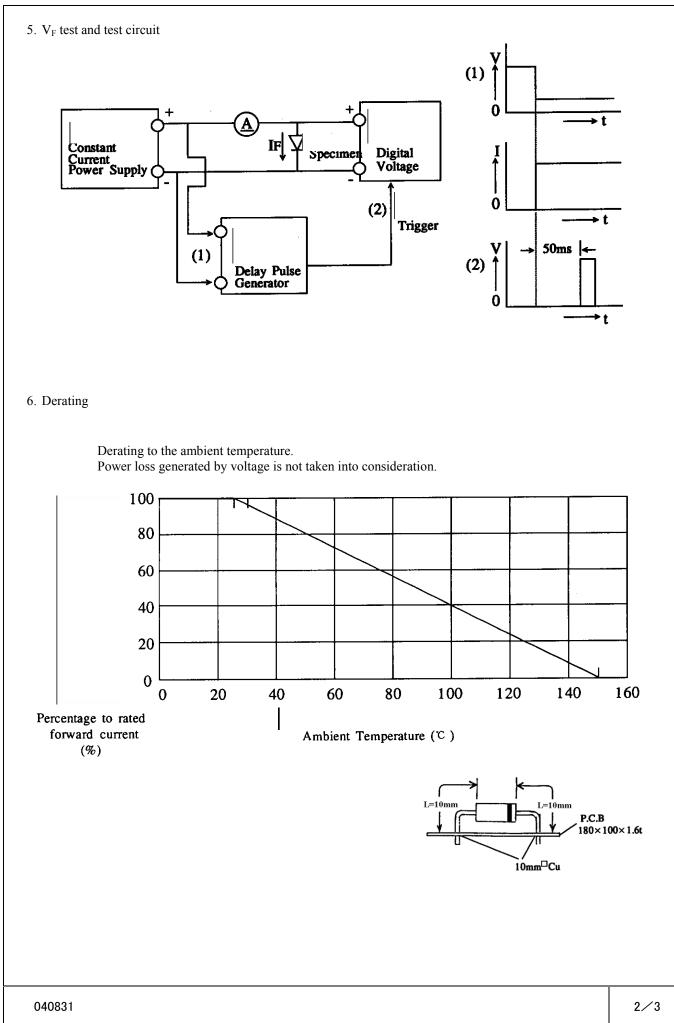
Туре	Silicon Rectifier Diode (Mesa type)				
Structure	Resin Molded Flammability: UL94V-0 (Equivalent)				
Applications	Pulse Rectification, etc				

3. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V _{RSM}	V	1050	
2	Peak Reverse Voltage	V _{RM}	V	1000	
3	Average Forward Current	I _{F(AV)}	А	0.2	Refer to Derating of 6
4	Peak Surge Forward Current	I _{FSM}	А	5	10msec. Sinewave, one shot
5	Junction Temperature	Tj	°C	-40~+150	
6	Storage Temperature	T _{stg}	°C	-40~+150	

4. Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V _F	V	4.0 max.	I _F =0.2A
2	Reverse Leakage Current	I _R	μΑ	5 max.	V _R =V _{RM}
3	Reverse Leakage Current Under High Temperature	H•I _R	μΑ	50 max.	V _R =V _{RM} , Ta=100°C
4	Reverse Recovery Time	trr-1	ns	200 max.	$I_F=I_{RP}=100$ mA, Ta=25°C 90% Recovery point
		trr-2	ns	80 max.	I_F =100mA, I_{RP} =200mA, Ta=25°C 75% Recovery point
5	Thermal Resistance	Rth(j-l)	°C /W	20.0 max.	Between Junction and Lead



7. Package information 7-1 Package type, physical dimensions and material **62.** 3^{□0.7} 5.0^{□0.2} Ľ₿ **60.**6 ¤0.05 □2 Ľ٦ ц Г j Dimensions in mm *1 The allowance position of Body against the center of whole lead wire is 0.5mm(max.) *2 The centric allowance of lead wire against center of physical body is 0.2mm(max.) *3 The burr may exit up to 2mm from the body of lead 7-2 Appearance The body shall be clean and shall not bear any stain, rust or flaw. 7-3 Marking ① Type number P0 as abbreviated of EP01C ② Class number : C Cathode Band ③ Lot number A: Last digit of calendar year B: Month (From 1 to 9 for Jan. to Sep. O for Oct. N for Nov. D for Dec.) (4) Ten days (• first ten days, • • second ten days, ... third ten days) 2 3 The type No. V_{RM} rank and Lot No. are to be marked in white. 4